

**Cascadable Amplifier**  
**10 to 500 MHz**

**A55/ SMA55**

V2

**Features**

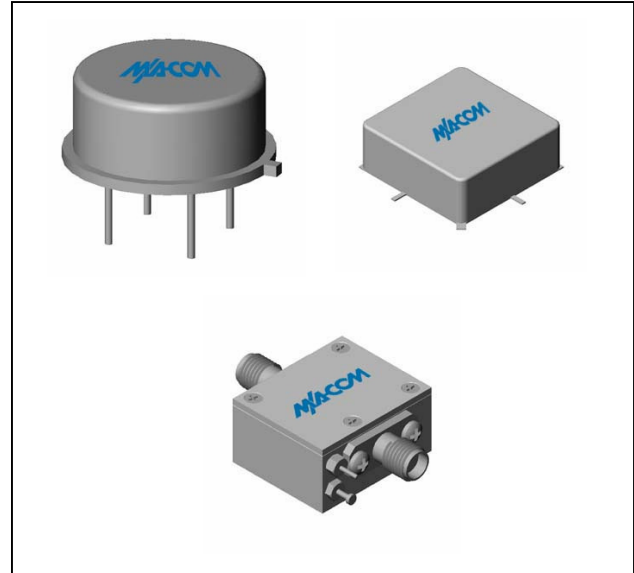
- AVAILABLE IN SURFACE MOUNT
- MEDIUM OUTPUT LEVEL: +11 dBm (TYP.)
- MEDIUM THIRD ORDER I.P. + 24 dBm (TYP.)

**Description**

The A55 RF amplifier is a discrete hybrid design, which uses thin film manufacturing processes for accurate performance and high reliability.

This single stage bipolar transistor feedback amplifier design displays impressive performance over a broadband frequency range. Both TO-8 and Surface Mount packages are Hermetically sealed, and MIL-STD-883 environmental screening is available.

**Product Image**



**Ordering Information**

Part Number	Package
A55	TO-8
SMA55	Surface Mount
CA55	SMA Connectorized

**Electrical Specifications:  $Z_0 = 50\Omega$ ,  $V_{CC} = +15 V_{DC}$**

Parameter	Units	Typical	Guaranteed	
		25°C	0° to 50°C	-54° to +85°C*
Frequency	MHz	5-600	10-500	10-500
Small Signal Gain (min)	dB	14.7	14.0	13.5
Gain Flatness (max)	dB	±0.5	±0.8	±1.0
Reverse Isolation	dB	20		
Noise Figure (max)	dB	5.0	6.0	6.5
Power Output @ 1 dB comp. (min)	dBm	11.0	9.0	8.0
IP3	dBm	+24		
IP2	dBm	+37		
Second Order Harmonic IP	dBm	+42		
VSWR Input / Output (max)		1.5:1 / 1.5:1	1.9:1 / 1.9:1	2.0:1 / 2.0:1
DC Current @ 15 Volts (max)	mA	30	35	37

**Absolute Maximum Ratings**

Parameter	Absolute Maximum
Storage Temperature	-62°C to +125°C
Case Temperature	+125°C
DC Voltage	+18 V
Continuous Input Power	13 dBm
Short Term Input power (1 minute max.)	50 mW
Peak Power (3 µsec max.)	0.5 W
"S" Series Burn-In Temperature (case)	+125°C

**Thermal Data:  $V_{CC} = +15 V_{DC}$**

Parameter	Rating
Thermal Resistance $\theta_{jc}$	45°C/W
Transistor Power Dissipation $P_d$	0.194 W
Junction Temperature Rise Above Case $T_{jc}$	9°C

\* Over temperature performance limits for part number CA55, guaranteed from 0°C to +50°C only.

